SKYPER 32



SKYPERTM

IGBT Driver Core

SKYPER 32

Preliminary Data

Features

- Two output channels
- Integrated potential free power supply
- Under voltage protection
- Drive interlock top / bottom
- Dynamic short cirucit protection
 DSCP
- Shut down input
- Failure management
- IEC 60068-1 (climate) 40/085/56

Typical Applications

- Driver for IGBT modules in bridge circuits in choppers, inverter drives, UPS and welding inverters
- DC bus voltage up to 1200 V

1) with external high voltage diode

- 2) according to EN50178
- 3) according to VDE 0110-20
- 4) can be expanded to 6,3µQ with boost capacitors

Isolation coordination in compliance with EN50178 PD2

Degree of protection: IP00

Technical Explanations to the driver core are available at www.semikron.com

Absolute Maximum Ratings						
Symbol	Conditions	Values	Units			
Vs	Supply voltage primary	16	V			
V _{iH}	Input signal voltage (High)	V _S + 0,3	V			
V _{iL}	Input signal voltage (Low)	GND - 0,3	V			
lout _{PEAK}	Output peak current	15	А			
lout _{AVmax}	Output average current	50	mA			
f _{max}	Max. switching frequency	50	kHz			
V _{CE}	Collector emitter voltage sense across the IGBT ¹⁾	1700	V			
dv/dt	Rate of rise and fall of voltage secondary to primary side	50	kV/µs			
V _{isollO}	Isolation test voltage input - output (AC, rms, 2s) 2)	4000	V			
VisoIPD	Partial discharge extinction voltage, rms, $Q_{PD} \le 10 pC^{-3}$	1500	V			
V _{isol12}	Isolation test voltage output 1 - output 2 (AC, rms, 2s) ²⁾	1500	V			
R _{Gonmin}	Minimum rating for R _{Gon}	1,5	Ω			
R _{Goffmin}	Minimum rating for R _{Goff}	1,5	Ω			
Q _{out/pulse}	Max. rating for output charge per pulse	2,5 ⁴⁾	μC			
T _{op}	Operating temperature	- 40 + 85	°C			
T _{stg}	Storage temperature	- 40 + 85	°C			

Characteristics		$T_a = 25 \text{ °C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
Vs	Supply voltage primary side	14,4	15	15,6	V
I _{so}	Supply current primary side (no load)	80			mA
	Supply current primary side (max.)			450	mA
V _i	Input signal voltage on/off		15 / 0		V
V _{iT+}	Input threshold voltage (High)			12,3	V
V _{iT-}	Input threshold voltage (Low)	4,6			V
R _{in}	Input resistance (switching signals)		10		kΩ
	Internal pull-up resistance shut down input (5V logic)		3,3		kΩ
V _{G(on)}	Turn on gate voltage output		+ 15		V
V _{G(off)}	Turn off gate voltage output		- 7		V
f _{ASIC}	Asic system switching frequency		8		MHz
t _{d(on)IO}	Input-output turn-on propagation time		1,1		μs
t _{d(off)IO}	Input-output turn-off propagation time		1,1		μs
t _{d(err)}	Error input-output propagation time	5,4		7,9	μs
t _{pERRRESET}	Error reset time		9		μs
t _{TD}	Top-Bot Interlock Dead Time		3		μs
V _{CEsat}	Reference voltage for V _{CE} -monitoring		10		V
C _{ps}	Coupling capacitance primary secondary	/	12		pF
w	weight		28		g
MTBF	Mean Time Between Failure @ T _a =40°C	'1	2,5		10 ⁶ h
	max. load				

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